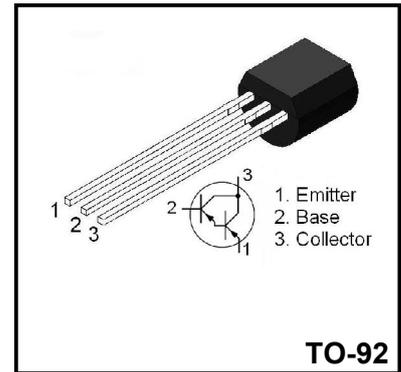


**PNP Plastic-Encapsulate Transistors  
Darlington Transistor**



**FEATURES**

- ♣ High current gain
- ♣ High collector current
- ♣ Complementary type: BC517

**Absolute Maximum Ratings (Ta=25°C)**

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$BV_{CBO}$	-40	V
Collector-Emitter Voltage	$BV_{CEO}$	-30	V
Emitter-Base Voltage	$BV_{EBO}$	-10	V
Collector Current	$I_C$	-1.0	A
Collector Power Dissipation	$P_C$	0.625	W
Junction Temperature	$T_j$	-55 ~ +150	°C
Storage Temperature	$T_{stg}$	-55 ~ +150	°C

**Electrical Characteristics (Ta=25°C)**

Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Collector-base breakdown voltage	$BV_{CBO}$	$I_C = -10\mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$BV_{CES}$	$I_C = -2mA, I_B = 0$	-30			V
Emitter-base breakdown voltage	$BV_{EBO}$	$I_E = -100nA, I_C = 0$	-10			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -30V, I_E = 0$			-100	nA
Collector cut-off current	$I_{CES}$	$V_{CE} = -30V, I_E = 0$			-500	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -10V, I_C = 0$			-100	nA
DC current gain	$h_{FE}$	$V_{CE} = -2V, I_C = -20mA$	20000			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -0.1mA$			1.0	V
Base-emitter on voltage	$V_{BE(on)}$	$V_{CE} = -5V, I_B = -10mA$			1.4	V
Transition frequency	$f_T$	$V_{CE} = -5V, I_C = -10mA, f = 100MHz$		200		MHz
Output capacitance	$C_{ob}$	$V_{CE} = -10V, f = 1MHz$		3.5		pF

Typical Characteristics

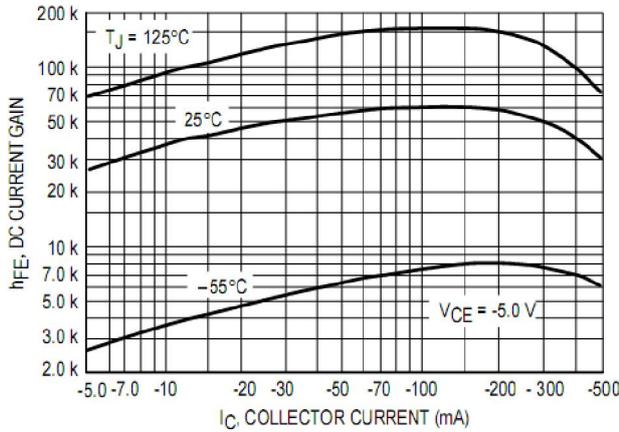


Figure 1. DC Current Gain

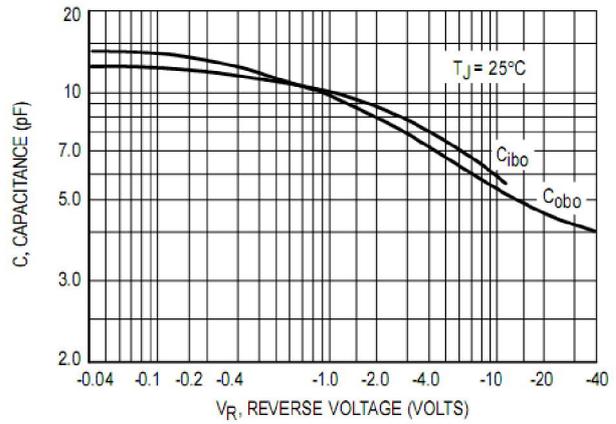


Figure 2. Capacitance

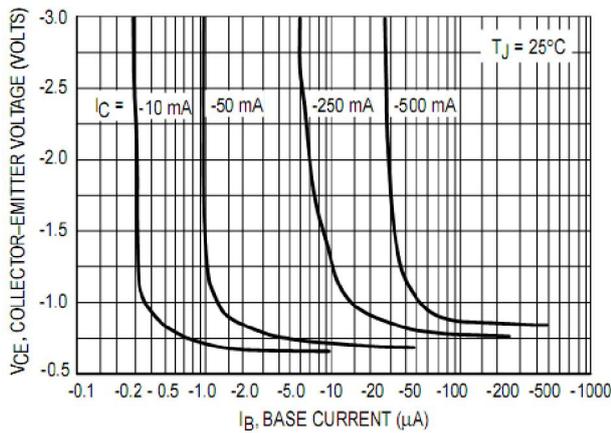


Figure 3. Collector Saturation Region

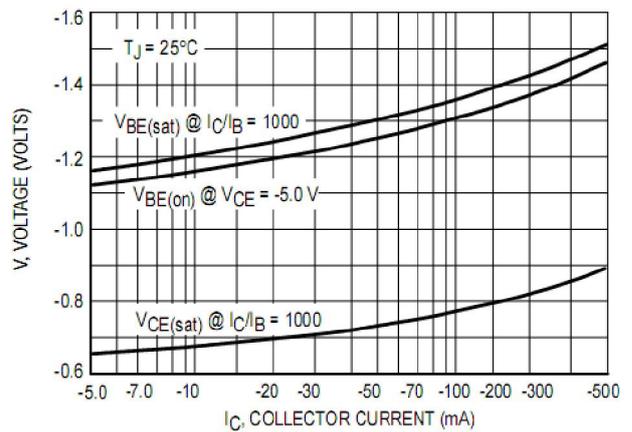


Figure 4. "On" Voltages

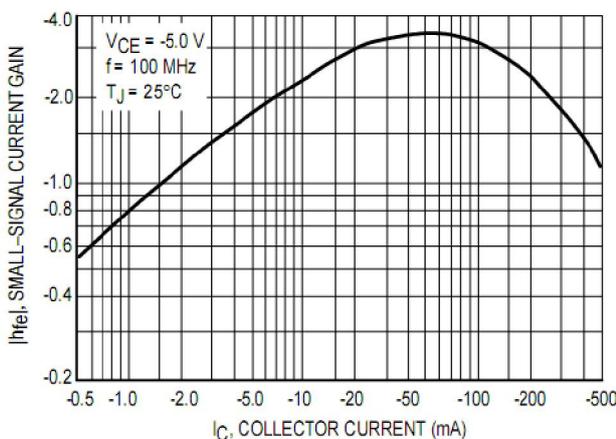


Figure 5. High Frequency Current Gain

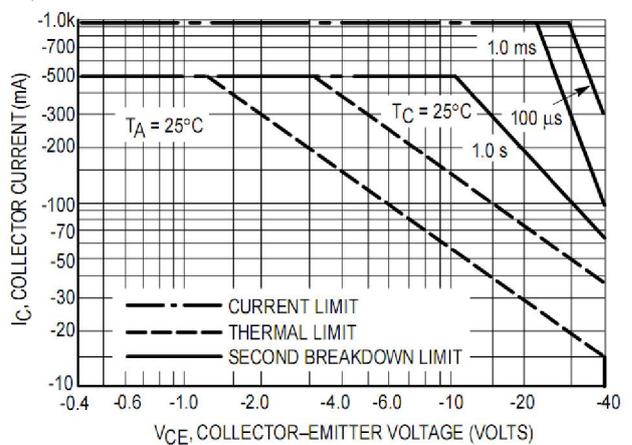
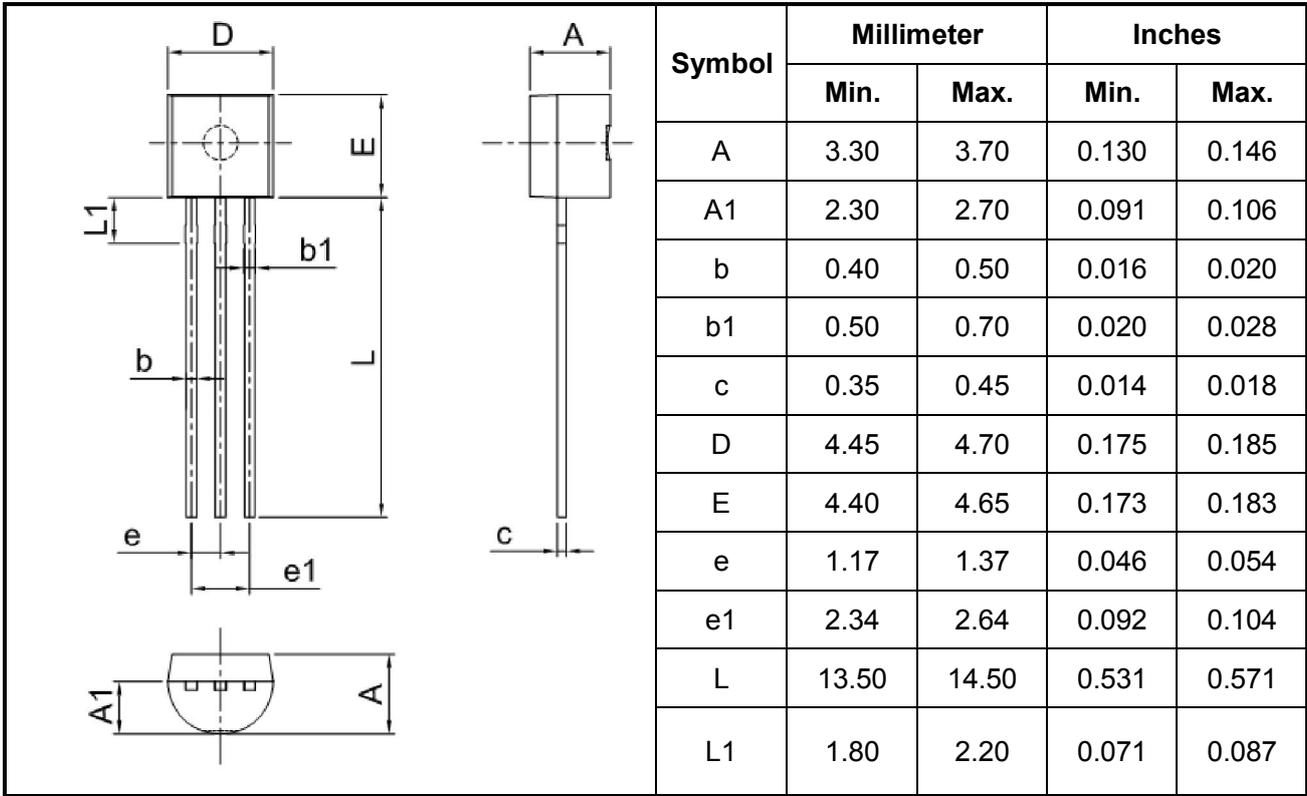


Figure 6. Active Region Safe Operating Area

Package Dimensions

TO-92



Package	Packing Method	Pack Quantity
TO-92	Bulk	1000pcs/Bag
TO-92	Tape	2000pcs/Box